



SEMIPONT® 2

Controllable Bridge Rectifiers

SKBT 40

Features

- Fully controlled single phase bridge rectifier
- Robust plastic case with screw terminals
- Large, isolated base plate
- Blocking voltage to 1400V
- High surge currents
- Easy chassis mounting
- UL recognized, file no. E 63 532

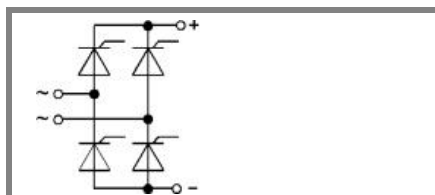
Typical Applications*

- For reversing DC drives
- Controlled field rectifiers for DC motors
- Controlled battery charger rectifiers

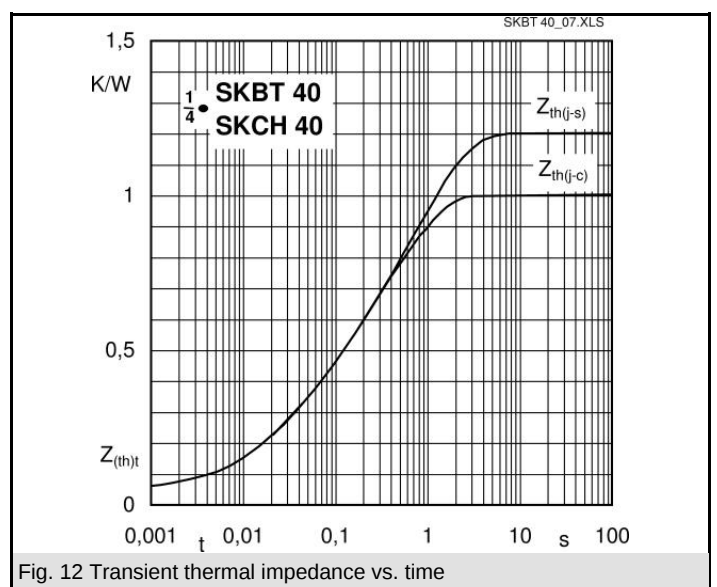
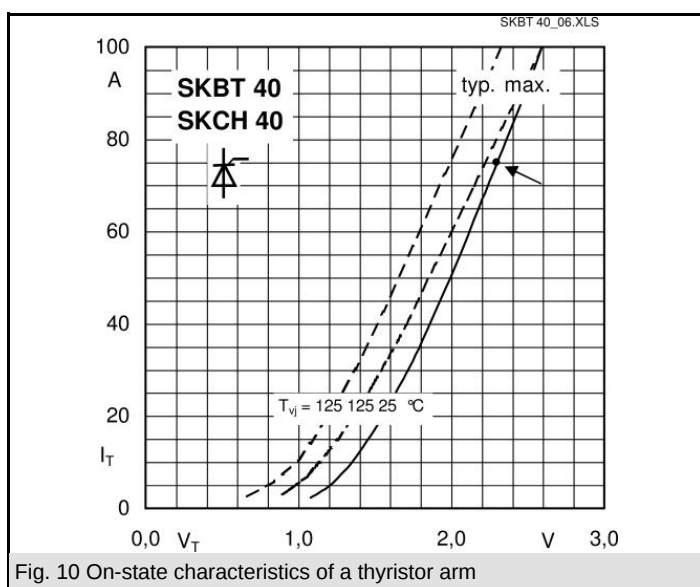
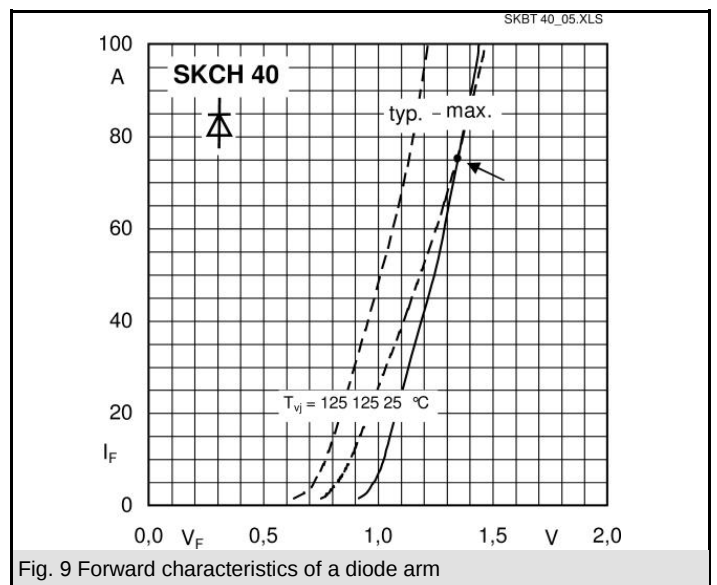
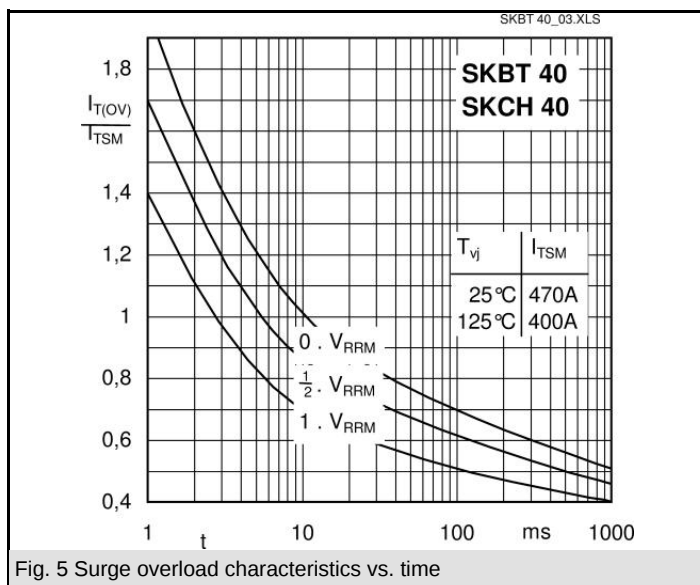
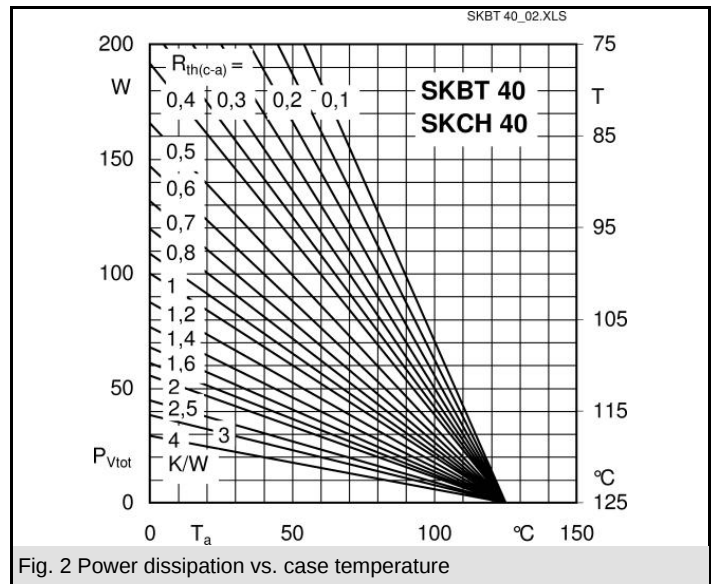
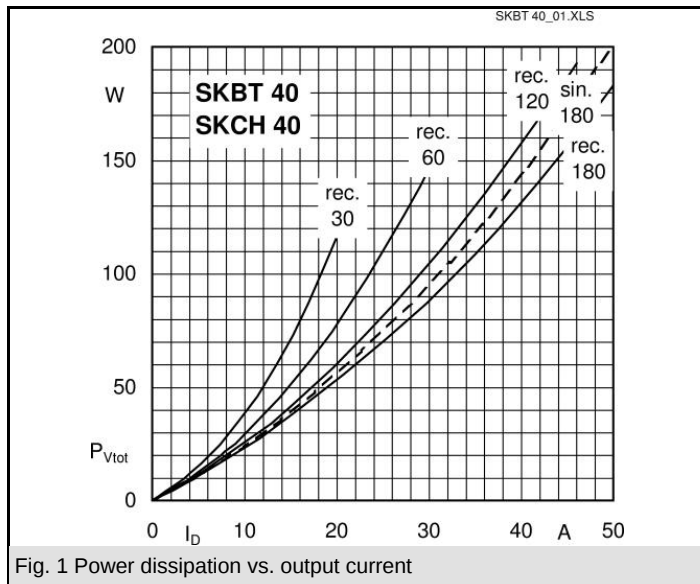
¹⁾ Painted metal shield of minimum 250 x 250 x 1 mm: $R_{th(c-a)} = 1,8 \text{ K/W}$

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_D = 40 \text{ A (full conduction)}$ ($T_c = 92^\circ \text{C}$)
800	800	SKBT 40/08
1200	1200	SKBT 40/12
1400	1400	SKBT 40/14

Symbol	Conditions	Values	Units
I_D	$T_c = 85^\circ \text{C}$	46	A
	$T_a = 45^\circ \text{C}$; chassis ¹⁾	15	A
	$T_a = 45^\circ \text{C}$; R4A/120	18	A
	$T_a = 45^\circ \text{C}$; P13A/125	18	A
	$T_a = 45^\circ \text{C}$; P1A/120	28	A
I_{TSM}, I_{FSM}	$T_{vj} = 25^\circ \text{C}$; 10 ms	470	A
	$T_{vj} = 125^\circ \text{C}$; 10 ms	400	A
i^2t	$T_{vj} = 25^\circ \text{C}$; 8,3 ... 10 ms	1100	A ² s
	$T_{vj} = 125^\circ \text{C}$; 8,3 ... 10 ms	800	A ² s
V_T	$T_{vj} = 25^\circ \text{C}$; $I_T = 75 \text{ A}$	max. 2,3	V
$V_{T(TO)}$	$T_{vj} = 125^\circ \text{C}$	max. 1	V
r_T	$T_{vj} = 125^\circ \text{C}$	max. 16	mΩ
I_{DD}, I_{RD}	$T_{vj} = 125^\circ \text{C}$; $V_{DD} = V_{DRM}$; $V_{RD} = V_{RRM}$	max. 10	mA
t_{gd}	$T_{vj} = 25^\circ \text{C}$; $I_G = 1 \text{ A}$; $di_G/dt = 1 \text{ A/μs}$	1	μs
t_{gr}	$V_D = 0,67 \cdot V_{DRM}$	1	μs
$(dv/dt)_{cr}$	$T_{vj} = 125^\circ \text{C}$	max. 500	V/μs
$(di/dt)_{cr}$	$T_{vj} = 125^\circ \text{C}$; $f = 50 \text{ Hz}$	max. 50	A/μs
t_q	$T_{vj} = 125^\circ \text{C}$; typ.	80	μs
I_H	$T_{vj} = 25^\circ \text{C}$; typ. / max.	100 / 200	mA
I_L	$T_{vj} = 25^\circ \text{C}$; $R_G = 33 \Omega$	250 / 400	mA
V_{GT}	$T_{vj} = 25^\circ \text{C}$; d.c.	min. 3	V
I_{GT}	$T_{vj} = 25^\circ \text{C}$; d.c.	min. 150	mA
V_{GD}	$T_{vj} = 125^\circ \text{C}$; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 125^\circ \text{C}$; d.c.	max. 5	mA
$R_{th(j-c)}$	per thyristor / diode	1	K/W
	total	0,25	K/W
$R_{th(c-s)}$	total	0,05	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 (3000)	V
M_s	to heatsink	5	Nm
M_t	to terminals	3	Nm
m		165	g
Case	SKBT	G 20	



SKBT



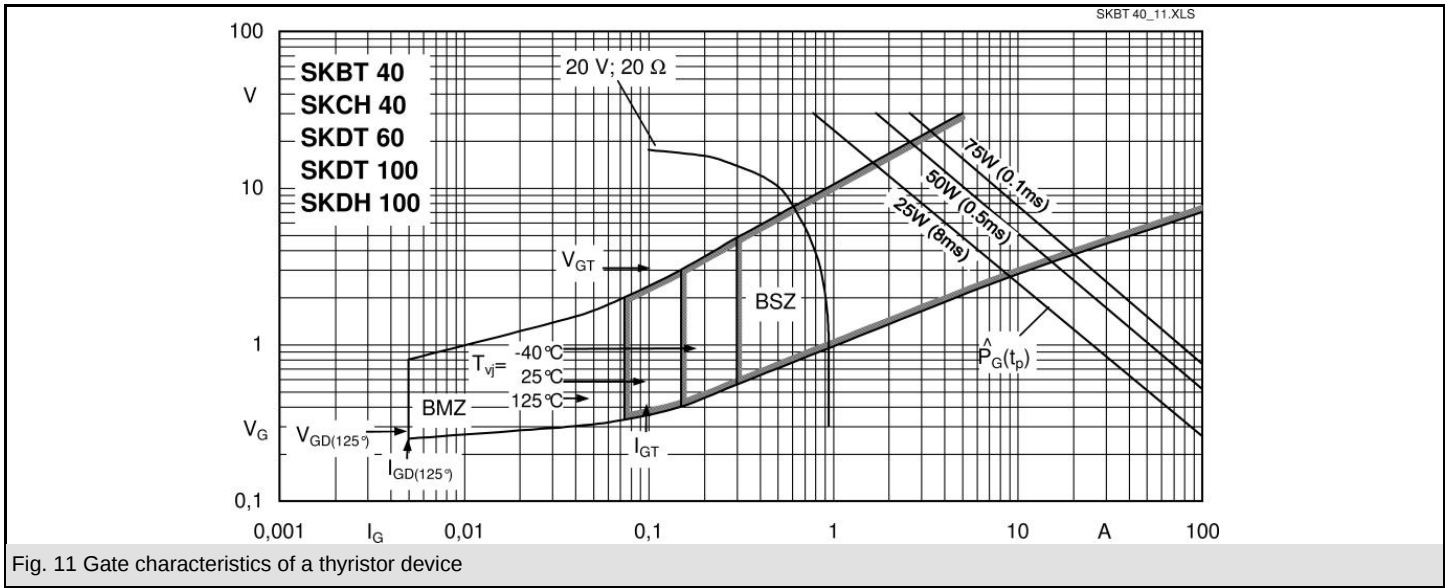
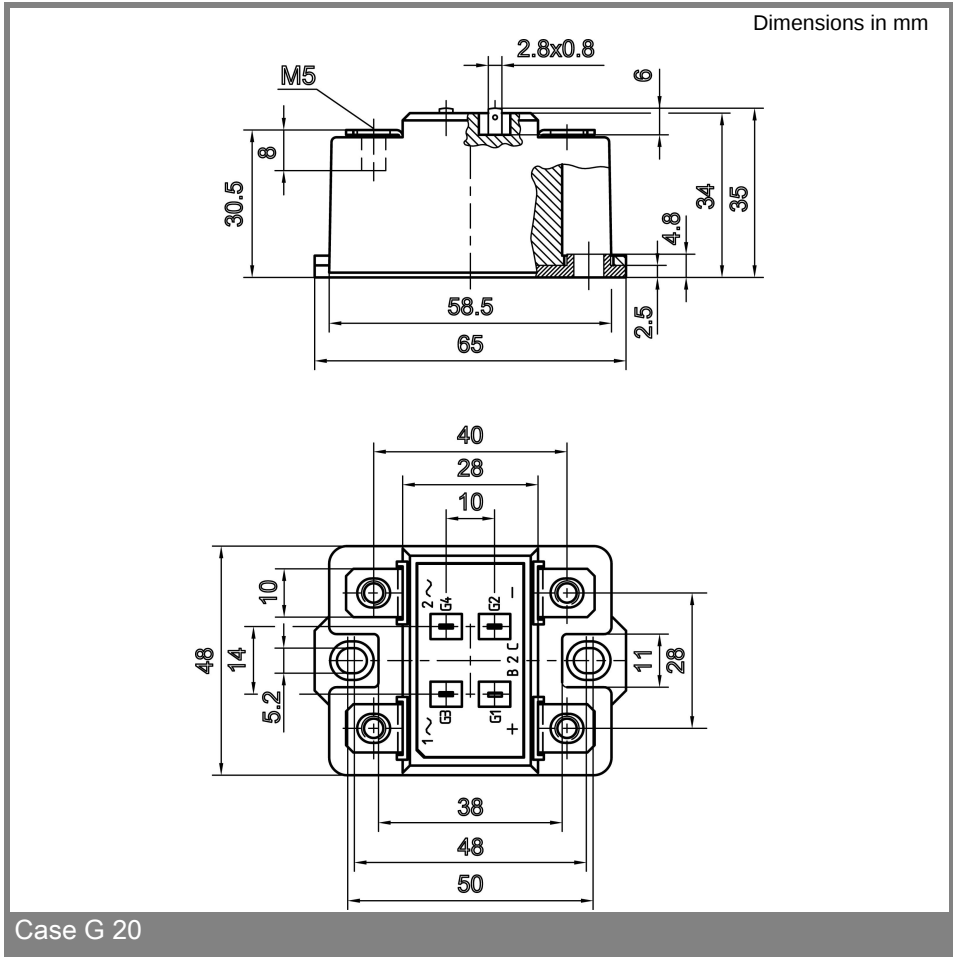


Fig. 11 Gate characteristics of a thyristor device



Case G 20

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.